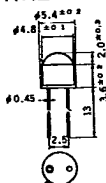
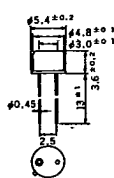


SILICON PIN PHOTODIODES

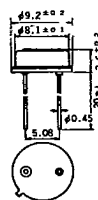
MI-11HL



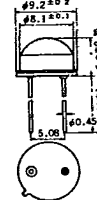
MI-11H



MI-33H



MI-33HL



Ta = 25°C

unit : mm

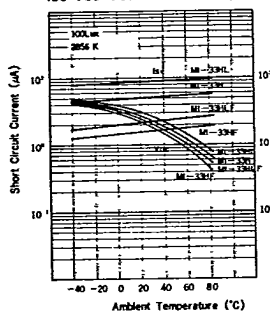
Maximum Ratings

Ratings	Symbol	MI-11H	MI-11HL	MI-33H	MI-33HL	Units
Reverse Voltage	V _R	30	30	32	32	V
Power Dissipation	P	25	25	200	200	mW
Operating Temperature	T _{opr.}	- 20 ~ + 80				°C
Storage Temperature	T _{stg.}	- 20 ~ + 80				°C

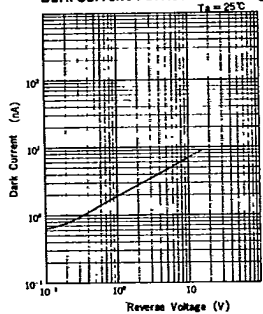
Characteristics

Ratings	Symbol	Conditions	MI-11H			MI-11HL		MI-33H			MI-33HL			Units
			MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	MIN.	TYP.	
Short Circuit Current	I _{sh}	2856K 1000Lux	5	8		20	50	40	55	70	80	110	140	μA
Dark Current	I _d	V _R = 10V R _H < 65%	1			1		5 50			5 50			nA
Peak Sensitivity Wavelength	λ _p		950			950		950			950			nm
Terminal Capacitance	C _t	V _R = 10V f = 1 MHz	4			4		15 20 25			15 20 25			pF
Response Time	tr. tf	V _R = 15V R _L = 1 kΩ	0.05			0.05		0.3			0.3			μs

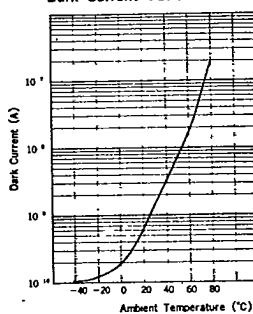
Isc-Voc VS. Ambient Temp.



Dark Current VS. Reverse Voltage



Dark Current VS. Ambient Temp.

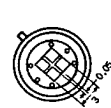


MUV-2537



(I_{sc}) 6 × 10⁻⁸ A (TYP) at 300 μW/cm²
 (V_{oc}) 900mV (TYP) at 300 μW/cm²
 (I_d) 1 × 10⁻¹¹ A (MAX) at V_R = 1 V
 (λ_p) 250nm

MI-33H-4D



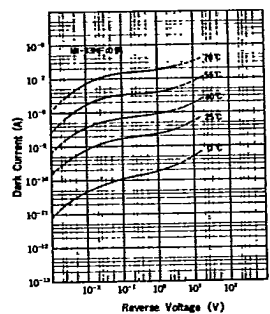
(I_{sc}) 1 14 μA (TYP.) at 1000Lux
 (I_d) 1 0.1 nA (TYP.) at V_R = 1 V
 (C_t) 1 7 pF (TYP.) f = 1MHz, V_R = 10V
 (λ_p) 930 nm

MI-33H-2D

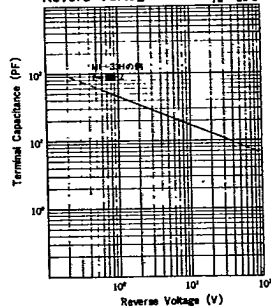


(I_{sc}) 1 30 μA (TYP.) at 1000Lux
 (I_d) 1 10nA (TYP.) at V_R = 1 V
 15% (MAX.)
 (λ_p) 930nm

Dark Current VS. Reverse Voltage



Terminal Capacitance VS. Reverse Voltage



Sensitivity Diagram

